



## SOT-89 Plastic-Encapsulated Transistors

### 2SB1188 TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$P_{CM}$ : 0.5 W ( $T_{amb}=25^{\circ}C$ )

Collector current

$I_{CM}$ : -2 A

Collector-base voltage

$V_{(BR)CBO}$ : -40 V

Operating and storage junction temperature range

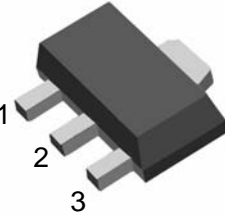
$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

#### SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu A, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-32		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu A, I_C=0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-20V, I_E=0$		-1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-4V, I_C=0$		-1	$\mu A$
DC current gain *	$h_{FE}$	$V_{CE}=-3V, I_C=-0.5A$	82	390	
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.2A$		-0.8	V
Transition frequency	$f_T$	$V_{CE}=-5V, I_C=-0.5A, f=30MHz$	80		MHz
Output capacitance	$C_{ob}$	$V_{CB}=-10V, I_E=0, f=1MHz$		65	pF

\* Measured using pulse current.

#### CLASSIFICATION OF $h_{FE}$

Rank	p	Q	R
Range	82-180	120-270	180-390
Marking	BCP	BCQ	BCR